

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	8	(circuit and pad and system and electrostatic near2 discharge near2 protection near2 system).clm.	US-PGPUB	OR	ON	2008/11/14 10:04
L2	0	(operational near2 requirement and electrostatic near2 discharge).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 10:02
L1	0	(operational near2 requirement and electrostatic near2 discharge and size).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 10:02
S98	74	S96 and S97	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 08:27
S97	4667	(361/56,91.1,111).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/14 08:26
S96	2799	(select selecting selected selection combine combining combination) near5 (length width size area) and (ESD electrostatic near2 discharge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 08:26
S95	20	hongwei near2 wang.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 08:24

S94	110	S93 and (ESD electrostatic near2 discharge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 08:23
S93	5096	broadcom near2 corporation.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 08:23
S92	113	(NMOS PMOS TRANSISTOR) near6 (clamp clamping shunt shunting ESD near3 protect \$4) with channel near4 (length width)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 08:11
S91	30	("4734752").URPN.	USPAT	OR	ON	2008/11/14 08:07
S90	1	("4342045").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/14 08:07
S89	29	S85 same (ESD electrostatic near2 discharge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 08:01
S88	8	S85 and S86	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 07:59
S87	1	S85 same S86	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 07:59
S86	445	ESD near2 requirement	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 07:59
S85	10959	operational near2 requirement	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 07:59

S84	1	10/668249	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/14 07:56
S83	420	(ESD electrostatic near2 discharge) and channel near3 length with channel near2 width	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 14:00
S82	515	(ESD electrostatic near2 discharge) and channel near3 length with width	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 14:00
S81	1344	(ESD electrostatic near2 discharge) and channel near3 length	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 14:00
S80	0	(ESD electrostatic near2 discharge) and channel near3 lenght	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:59
S79	0	(ESD electrostatic near2 discharge) and channel near3 lenght with width	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:59
S78	0	(ESD electrostatic near2 discharge) and channel near3 lenght with channel near2 width	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:59
S77	212	(ESD electrostatic near2 discharge) and S76	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:46

S76	44594	(combine combined) near4 (area size)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:46
S75	823	S70 and S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:30
S74	3060	(361/56).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/13 13:29
S73	4823	(ESD electrostatic near2 discharge) with (area size)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:29
S72	0	S70 and width with lenght	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:29
S71	0	S70 same width with lenght	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:29
S70	8270	(ESD electrostatic near2 discharge) same (area size)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/13 13:28

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